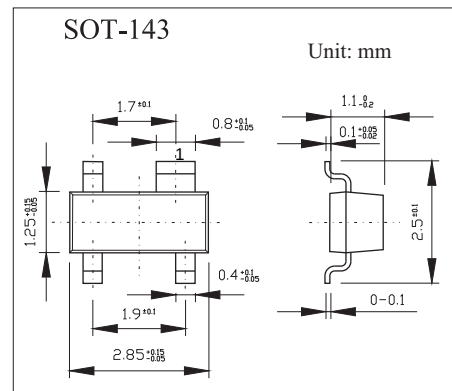
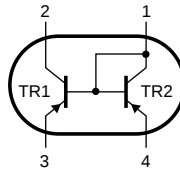


PNP general purpose double transistor BCV62

■ Features

- High current gain
- Low collector-emitter saturation voltage



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-30	V
Collector-emitter voltage	V_{CE0}	-30	V
Emitter-base voltage	V_{EB0}	-6	V
Collector current	I_c	-100	mA
Power dissipation	P_D	250	mW
Thermal resistance from junction to ambient	$R_{\theta JA}$	500	$^\circ\text{C}/\text{W}$
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

BCV62

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Transistor TR1						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -10\ \mu A, I_E = 0$	-30			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10\ mA, I_B = 0$	-30			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_C = -10\ \mu A, I_C = 0$	-6			V
Collector cutoff current	I_{CBO}	$V_{CB} = -30V, I_E = 0$			-15	nA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-100	nA
DC current gain	h_{FE}	$V_{CE} = -5V, I_C = -100\ \mu A$	100			
		$V_{CE} = -5V, I_C = -2mA$	100		800	
collector-emitter saturation voltage *	$V_{CE(sat)}$	$I_C = -10\ mA; I_B = -0.5\ mA$			-0.3	V
		$I_C = -100\ mA; I_B = -5\ mA$			-0.65	V
base-emitter saturation voltage *	$V_{BE(sat)}$	$I_C = -10\ mA; I_B = -0.5\ mA$		-0.7		V
		$I_C = -100\ mA; I_B = -5\ mA$		-0.85		V
Collector capacitance	C_c	$I_E = I_C = 0; V_{CB} = -10\ V; f = 1\ MHz$		4.5		pF
Transition frequency	f_T	$I_C = -10\ mA; V_{CE} = -5\ V; f = 100\ MHz$	100			MHz
Noise figure	F	$I_C = -200\ \mu A; V_{CE} = -5\ V; R_s = 2k\ \Omega; f = 1\ kHz; B = 200\ Hz$			10	dB
Transistor TR2						
Base-emitter forward voltage	V_{EBS}	$V_{CB} = 0; I_E = 250\ mA$			1.5	V
		$V_{CB} = 0; I_E = 10\ \mu A$	0.4			mV
DC current gain	h_{FE}	$I_C = -2\ mA; V_{CE} = -5\ V$	125		250	
BCV62A			220		475	
BCV62B			420		800	
BCV62C						

* pulse test: Pulse Width $\leq 300\ \mu s$, Duty Cycle $\leq 2.0\%$.

■ Marking

TYPE	BCV61	BCV61A	BCV61B	BCV61C
Marking	3MP	3JP	3KP	3LP

BCV62

■ Typical Characteristics

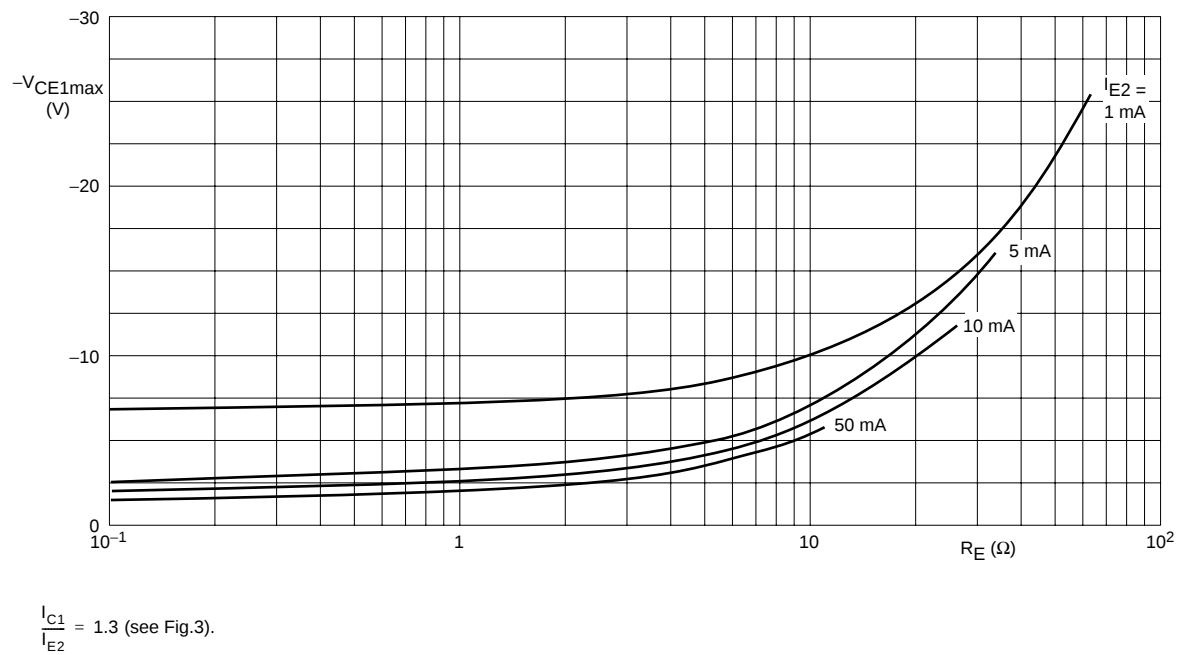


Fig.1 Maximum collector-emitter voltage as a function of emitter resistance.